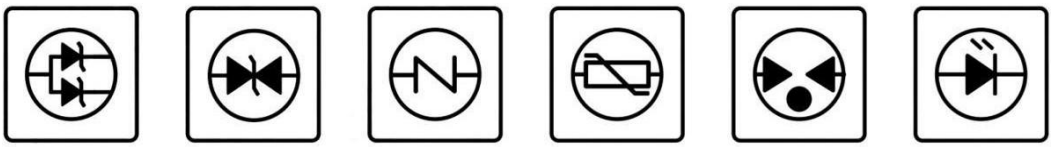
MSKSEMI 美森科
SEMICONDUCTOR



IRFR220N(MS)

Product specification

DESCRIPTION

The IRFR220N(MS) uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

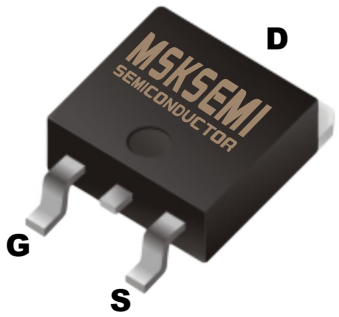
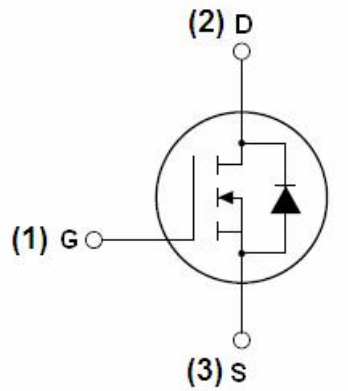
General Features

- V_{DS} =200V,I_D =8A
  $R_{DS(ON)}$ <300mΩ @ V_{GS}=10V（Typ：260mΩ）
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Low gate to drain charge to reduce switching losses

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Reference News

PACKAGE OUTLINE	Schematic Diagram	Marking
		MSKSEMI IRFR220N MS XXX Notes :XXX represents the order code

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	8	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	5.6	A
Pulsed Drain Current	I_{DM}	20	A
Maximum Power Dissipation	P_D	55	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case(Note 2)	$R_{\theta JC}$	2.3	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

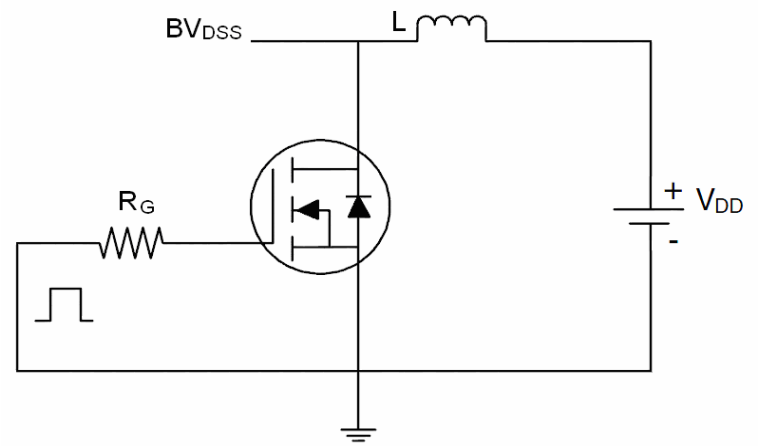
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage V_{GS}=0V I_D=250μA			200	215	-	V
Zero Gate Voltage Drain Current V_{DS}=200V,V_{GS}=0V			-	-	1	μA
Gate-Body Leakage Current V_{GS}=±20V,V_{DS}=0V			-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage V_{DS}=V_{GS},I_D=250μA			1	1.7	2.5	V
Drain-Source On-State Resistance V_{GS}=10V, I_D=4.5A			-	260	300	mΩ
Forward Transconductance V_{DS}=25V,I_D=4.5A			3	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0 V, F= 1.0MHz		540		PF
Output Capacitance	C_{oss}			90		PF
Reverse Transfer Capacitance	C_{rss}			35		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=100V,I_D=4.5 A V_{GS}=10V,R_{GEN}=5 Ω	-	6.4	-	nS
Turn-on Rise Time	t_r		-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	V_{DS}=160V,I_D=4.5 A, V_{GS}= 10V	-	16	-	nC
Gate-Source Charge	Q_{gs}		-	3.4	-	nC
Gate-Drain Charge	Q_{gd}		-	5.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=8A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	8	A

Notes:

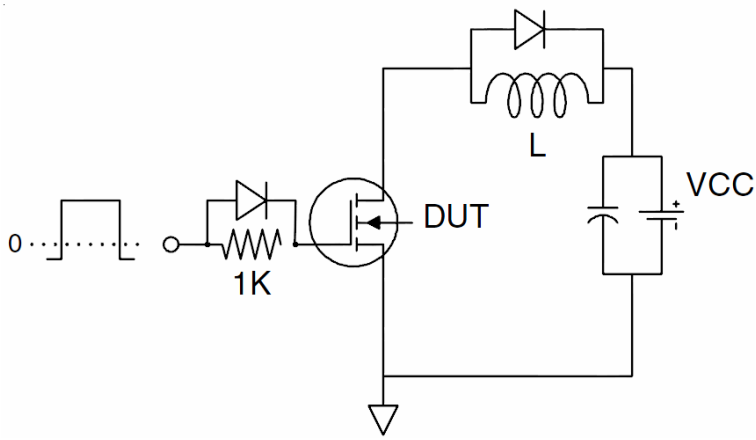
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

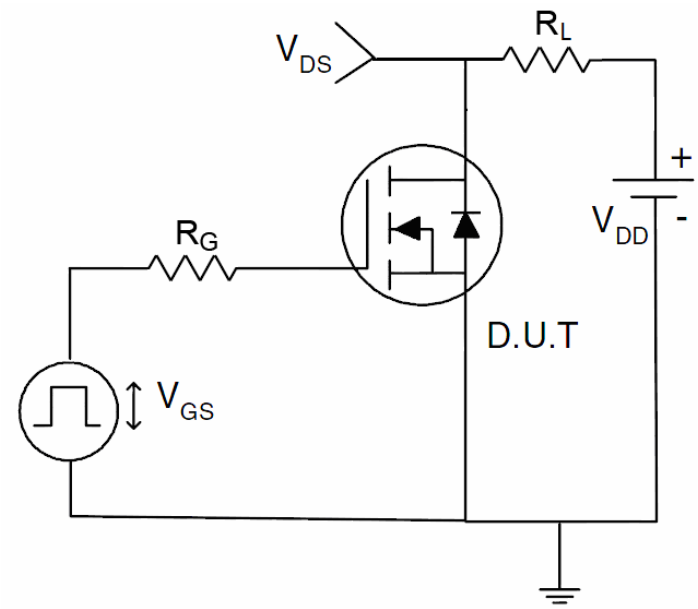
1）E_{AS} test Circuit



2）Gate charge test Circuit



3）Switch Time Test Circuit



TypicalElectricalandThermal Characteristics (Curves)

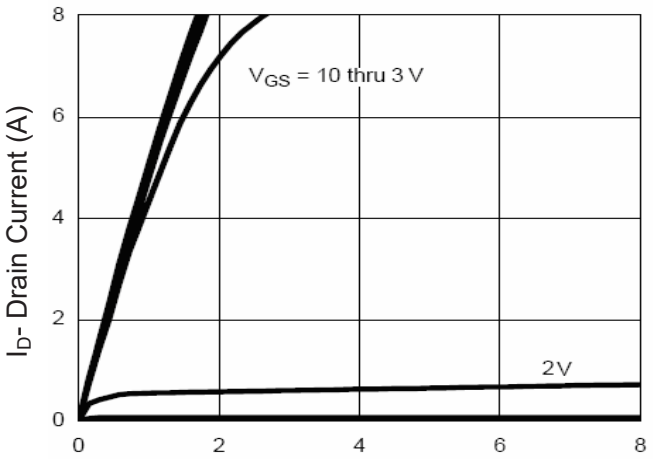


Figure 1 Output Characteristics

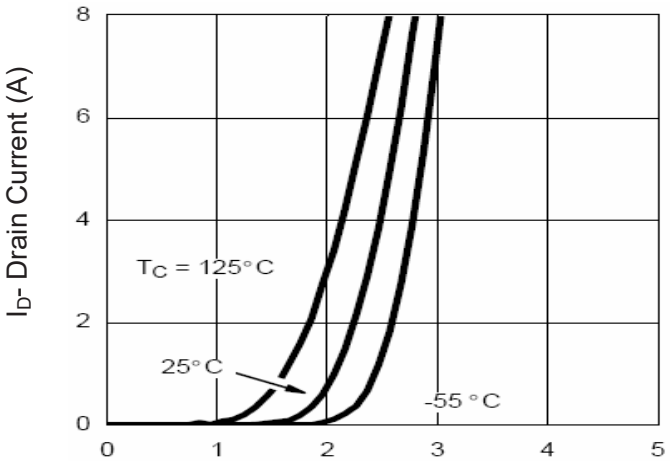


Figure 2 Transfer Characteristics

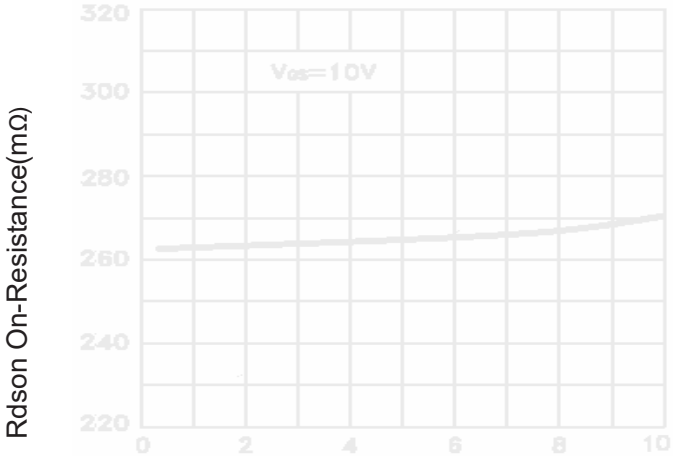


Figure 3 Rdson- Drain Current

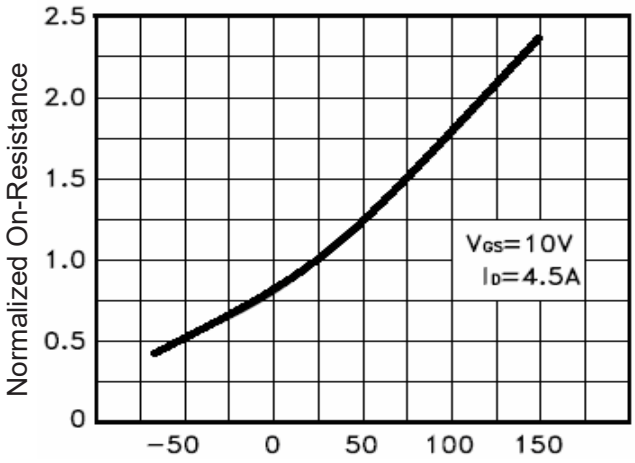


Figure 4 Rdson-JunctionTemperature

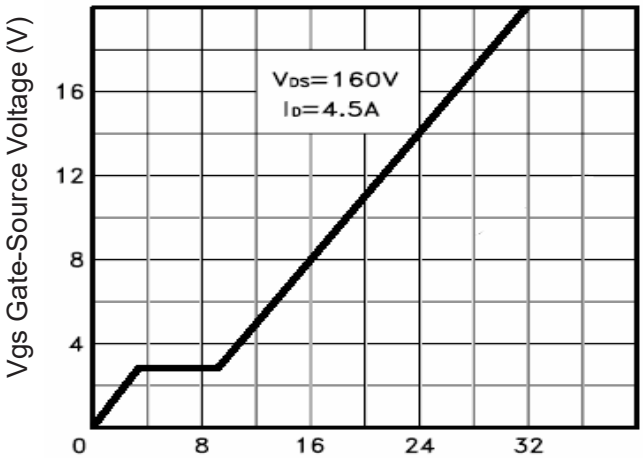


Figure 5 Gate Charge

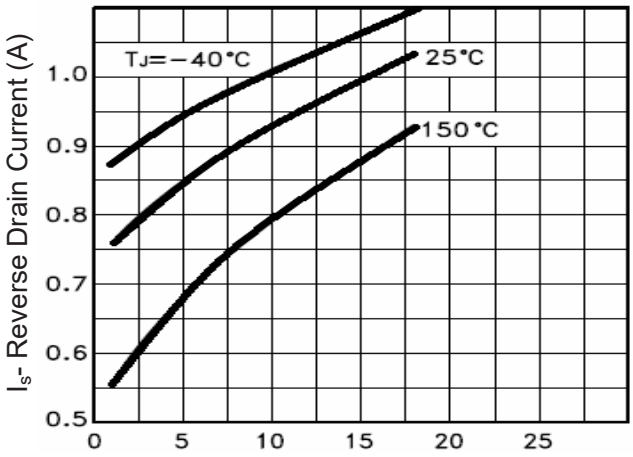


Figure 6 Source- Drain Diode Forward

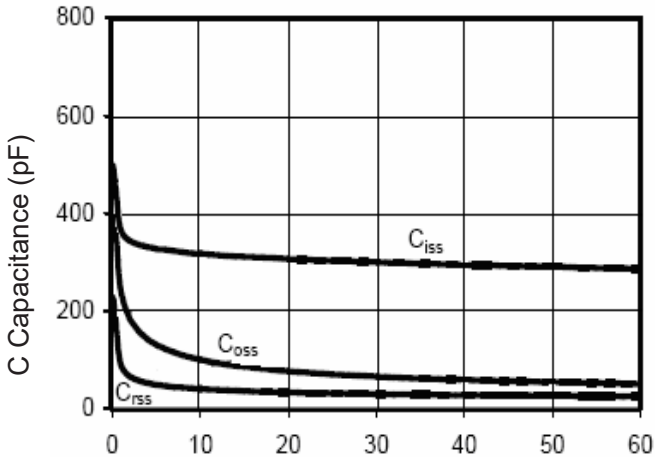


Figure 7 Capacitance vs Vds

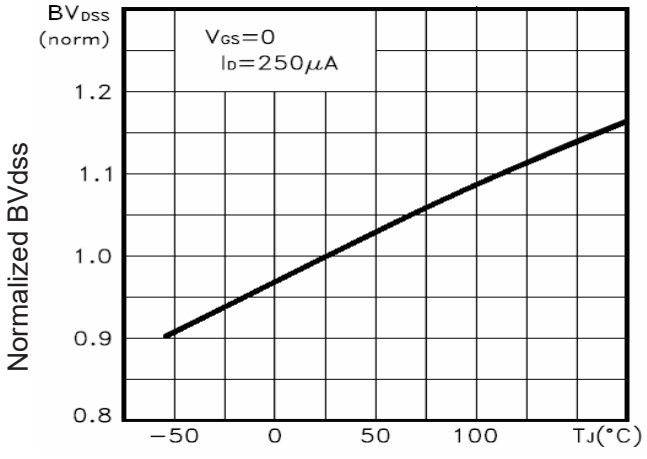


Figure 9 BV_{DSS} vs Junction Temperature

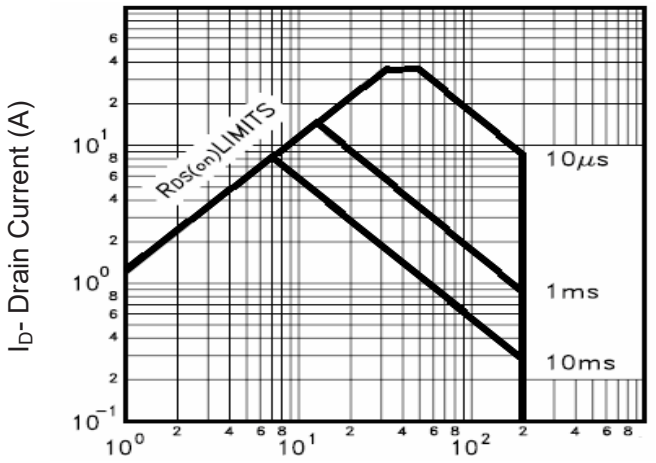


Figure 8 Safe Operation Area

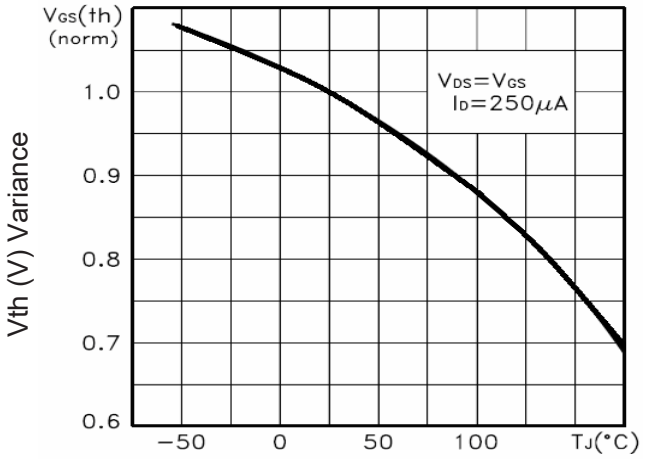


Figure 10 $V_{GS(th)}$ vs Junction Temperature

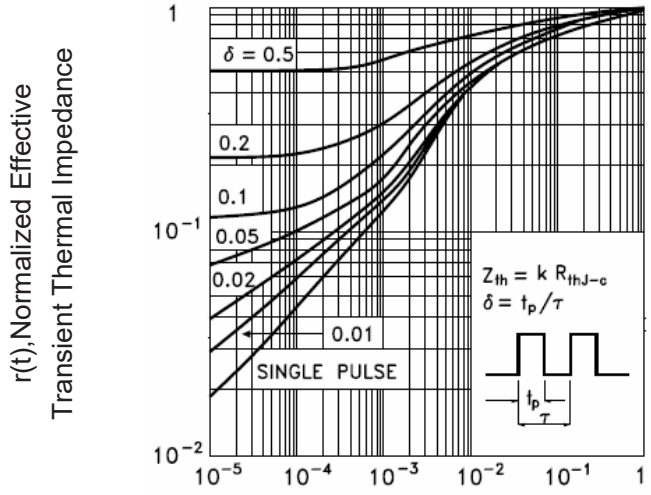
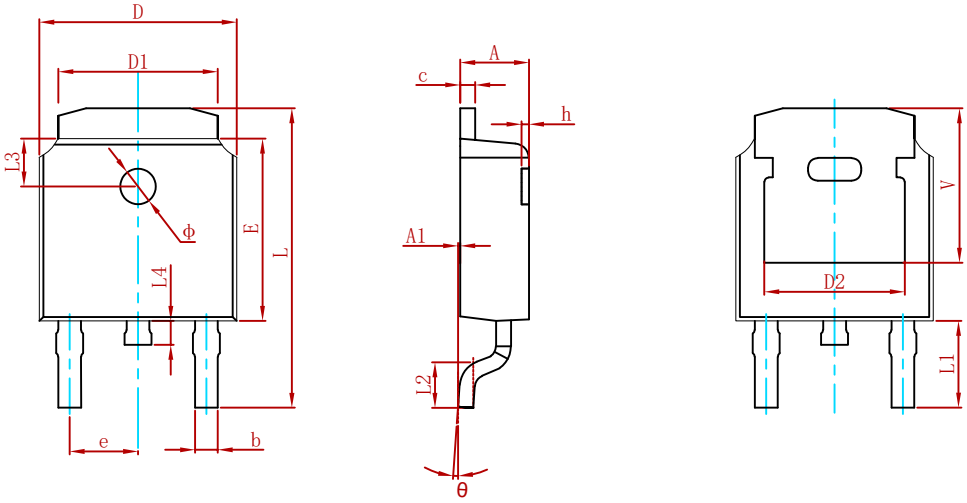


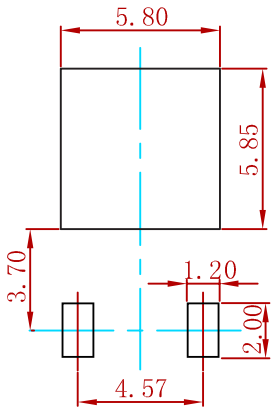
Figure 11 Normalized Maximum Transient Thermal Impedance

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
IRFR220N(MS)	TO-252	2500

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